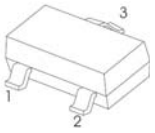
SI2300

N-Channel Enhancement Mode Field Effect Transistor

FEATURE

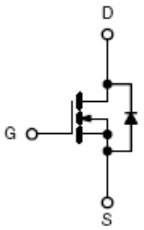
- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

SOT-23



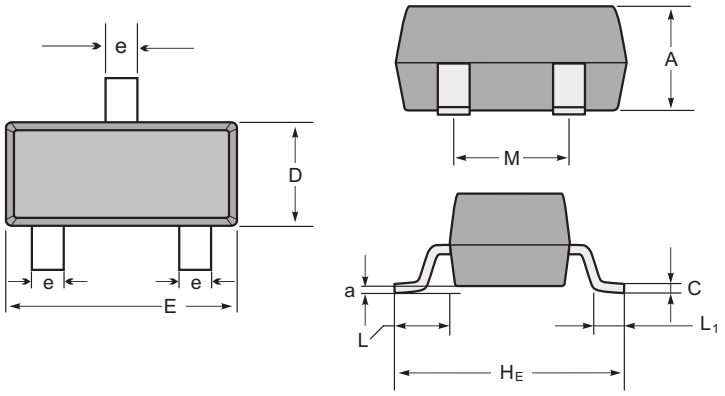
1. GATE
2. SOURCE
3. DRAIN

Equivalent Circuit



Marking

Type number	Marking code
SI2300	2300



SOT-23 mechanical data

UNIT		A	C	D	E	H_E	e	M	L	L_1	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Maximum Body-Diode Continuous Current	I_S	2	
Maximum Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~+150	

SI2300

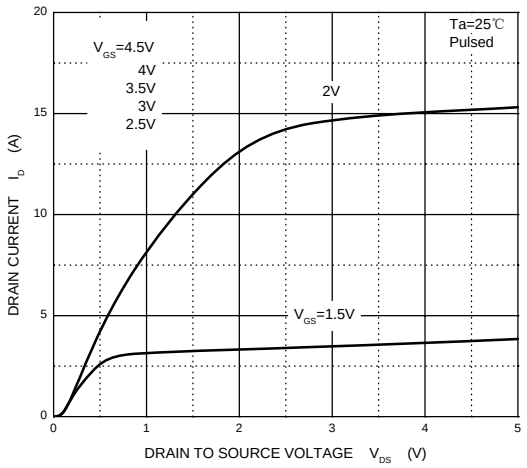
T_a=25℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Gate-source leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±12V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =16V, V_{GS} =0V			1.0	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.5	0.7	1.0	V
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} =4.5V, I_D =5.0A		22	27	mΩ
		V_{GS} =2.5V, I_D =4.0A		35	42	
		V_{GS} =1.8V, I_D =2.0A			73	
Diode forward voltage	V_{SD}	V_{GS} =0V,I_S=1A		0.75	1	V
Forward transconductance	g_{fS}	V_{DS} =5V, I_D =3.8A	4			S
DYNAMIC PARAMETERS*						
Input capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f =1MHz		630		pF
Output capacitance	C_{oss}			164		
Reverse transfer capacitance	C_{rss}			137		
Gate resistance	R_g	V_{DS} =0V,V_{GS} =0V,f =1MHz		1.5		Ω
SWITCHING PARAMETERS*						
Turn-on delay time	$t_{d(on)}$	V_{GS}=5V,V_{DS}=10V, R_L=1.7Ω,R_{GEN}=6Ω		5.5		ns
Rise time	t_r			14		
Turn-off delay time	$t_{d(off)}$			29		
Fall time	t_f			10.2		

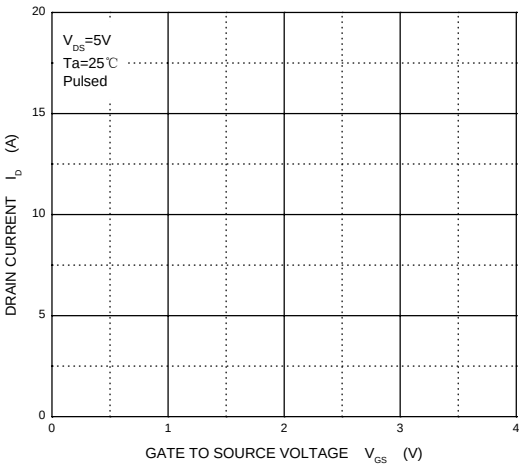
*These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES (SI2300)

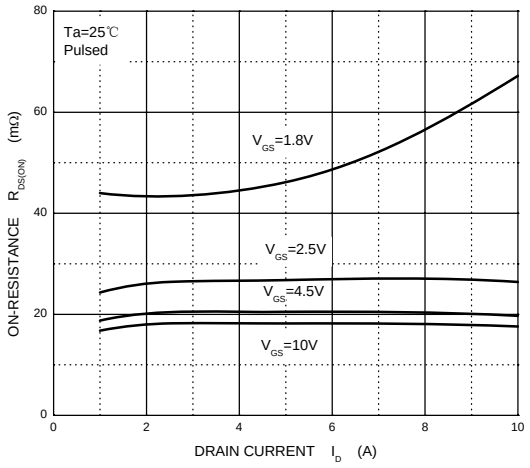
Output Characteristics



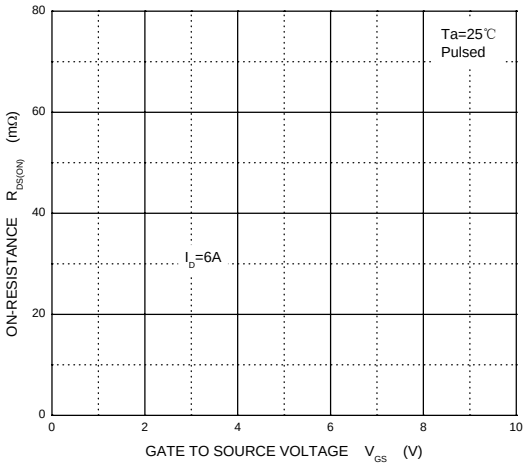
Transfer Characteristics



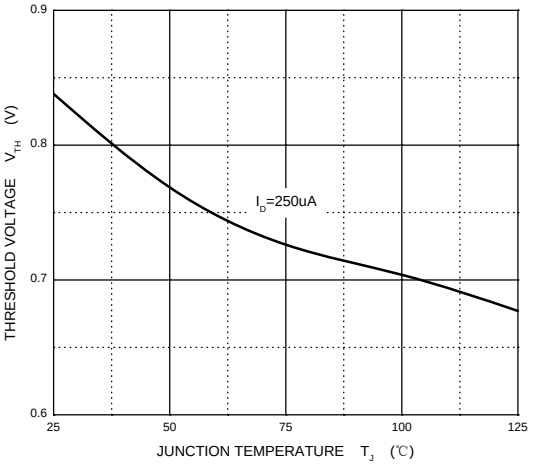
$R_{DS(ON)}$ —— I_D



$R_{DS(ON)}$ —— V_{GS}



Threshold Voltage



I_S —— V_{SD}